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MICR131.0

09/503,638

Applicant(s)

Kirk D. Prall

Filing Date

2/14/00

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U.S. PATENT DOCUMENTS

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Serial No. 09/503,638

COPIES OF THE CITED REFERENCES ON THE ATTACHED INFORMATION
DISCLOSURE CITATION WERE PREVIOUSLY CITED BY OR SUBMITTED TO
THE PATENT OFFICE IN THE PARENT APPLICATION, WHICH IS U.S.
PATENT APPLICATION SERIAL NO. 08/868,058 FILED JUNE 3, 1997,
WHICH IS A DIVISIONAL OF U.S. PATENT APPLICATION SERIAL NO.
08/399,843 FILED MARCH 7, 1995.

INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)

Docket Number (Optional)

MICR131

Application Number

Applicant(s)

Kirk D. Prall, et al.

Filing Date

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09/503638



02/14/00

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
JP		4,709,467	12/1/87	Liu	437	30	
JP		4,512,073	4/23/85	Hsu	29	571	
JP		5,168,073	12/1/92	Gonzalez et al.	437	47	
JP		5,240,872	8/31/93	Motanomi et al.	437	52	
JP		5,126,916	6/30/92	Tseng	361	313	
JP		5,244,826	9/14/93	Gonzalez et al.	437	60	
JP		5,376,566	12/27/94	Gonzalez	437	35	
JP		5,234,856	10/10/93	Gonzalez	437	47	
JP		5,227,325	7/13/93	Gonzalez	437	52	
JP		5,320,974	6/14/94	Hori et al.	437	44	
JP		5,250,832	10/5/93	Murai	257	306	

FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
JP	60-253274	12/13/85	Japan	437	40 AS		

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

JP		Hurkx et al., A New Recombination Model for Device Simulation Including Tunneling, IEEE TRED Vol. 39, No. 2 Feb. 1992, pages 331-338.
JP		Hurkx, Anomalous Behaviour of Surface Leakage Currents in Heavily Doped Gated Diodes, IEEE TRED Vol. 40, No. 12, Dec. 1993, pages 2273-2281.
EXAMINER	DATE CONSIDERED	
	8/24/01	

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Kirk D. Prall et al.

Filing Date:

June 3, 1997

Group Art Unit

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